NSN 5961-01-116-8470



Diode Semiconductor Device - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-116-8470 **Inclosure Material:** Metal **Overall Length:** 0.625 inches **Overall Diameter:** 0.675 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-228 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 reverse voltage, dc **Current Rating Per Characteristic:** 30.00 amperes forward current, average absolute **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Precious Material And Location:** External surfaces gold **Precious Material:** Gold **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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